



GaAs pHEMT MMIC 1 WATT POWER AMPLIFIER, DC - 6 GHz

Typical Applications

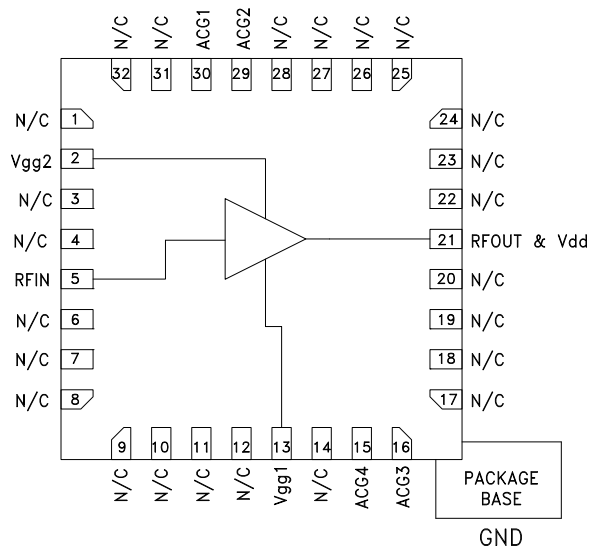
The HMC637ALP5E wideband PA is ideal for:

- Telecom Infrastructure
- Microwave Radio & VSAT
- Military & Space
- Test Instrumentation
- Fiber Optics

Features

- P1dB Output Power: +29 dBm
- Gain: 13 dB
- Output IP3: +44 dBm
- 50 Ohm Matched Input/Output
- 32 Lead 5x5mm Lead SMT Package: 25 mm²

Functional Diagram



General Description

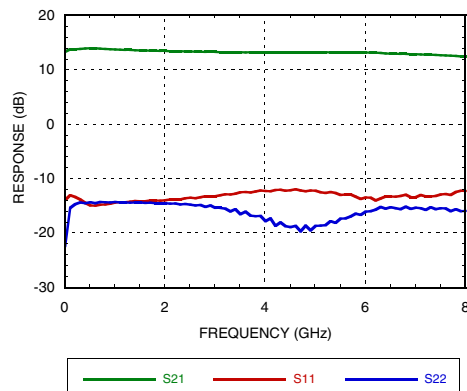
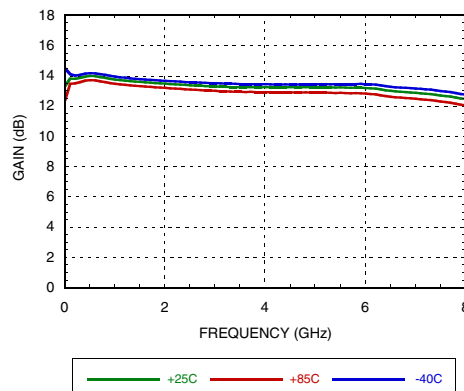
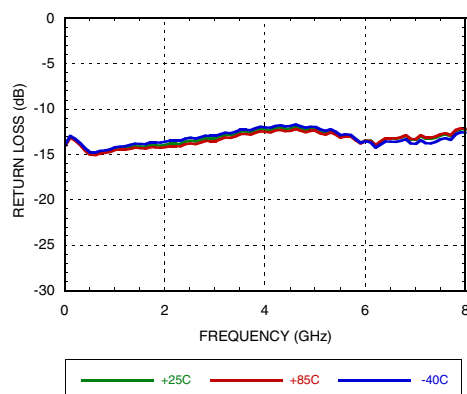
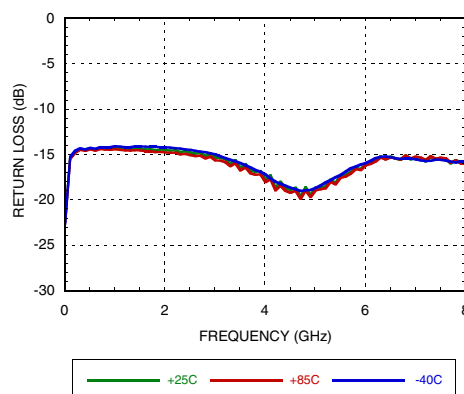
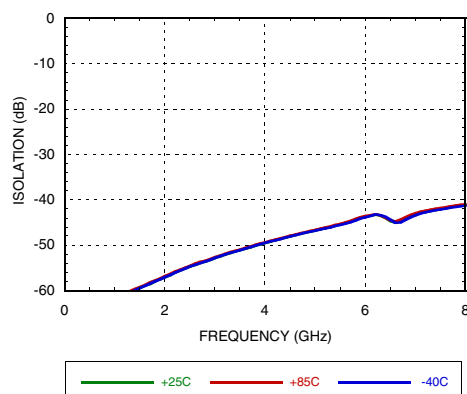
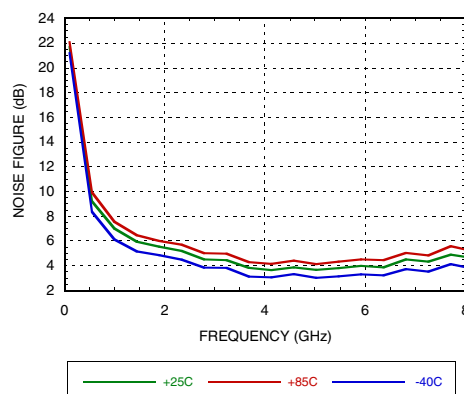
The HMC637ALP5E is a GaAs MMIC pHEMT Distributed Power Amplifier which operates between DC and 6 GHz. The amplifier provides 13 dB of gain, +44 dBm output IP3 and +29 dBm of output power at 1 dB gain compression while requiring 400 mA from a +12V supply. Gain flatness is excellent at ± 0.75 dB from DC - 6 GHz making the HMC637ALP5E ideal for EW, ECM, Radar and test equipment applications. The HMC637ALP5E amplifier I/Os are internally matched to 50 Ohms and the 5x5 mm QFN package is compatible with high volume SMT assembly equipment.

Electrical Specifications, $T_A = +25^\circ\text{C}$, $V_{dd} = +12\text{V}$, $V_{gg2} = +5\text{V}$, $I_{dd} = 400\text{ mA}$ ^[1]

| Parameter | Frequency | Min. | Typ. | Max. | Units |
|--|-------------------------------|------|------------|------|----------|
| Gain | DC - 6.0 GHz | 12 | 13 | | dB |
| Gain Flatness | DC - 6.0 GHz | | ± 0.75 | | dB |
| Gain Variation Over Temperature | DC - 6.0 GHz | | 0.015 | | dB/°C |
| Input Return Loss | DC - 6.0 GHz | | 12 | | dB |
| Output Return Loss | DC - 6.0 GHz | | 15 | | dB |
| Output Power for 1 dB Compression (P1dB) | DC - 6.0 GHz | 27 | 29 | | dBm |
| Saturated Output Power (Psat) | DC - 6.0 GHz | | 31 | | dBm |
| Output Third Order Intercept (OIP3) ^[2] | DC - 6.0 GHz | | 44 | | dBm |
| Noise Figure | DC - 2.0 GHz 2.0 - 6.0 GHz | | 12 5 | | dB dB |
| Supply Current (Idd) | | 320 | 400 | 480 | mA |

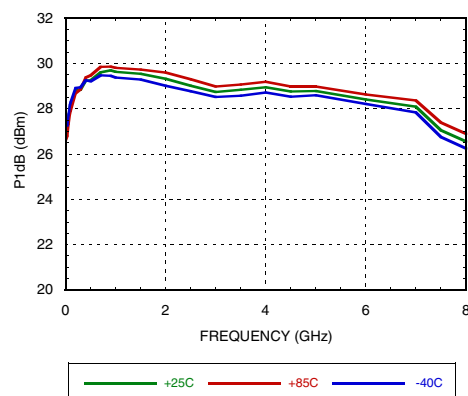
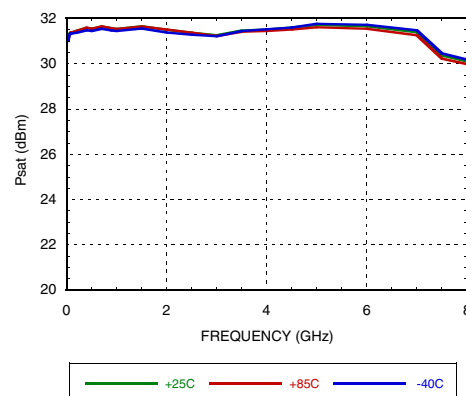
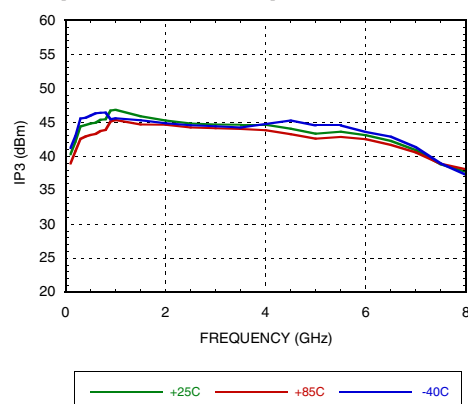
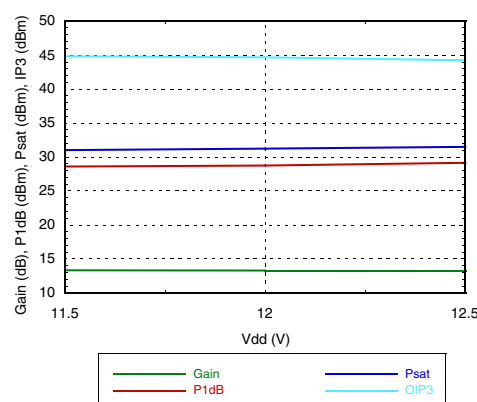
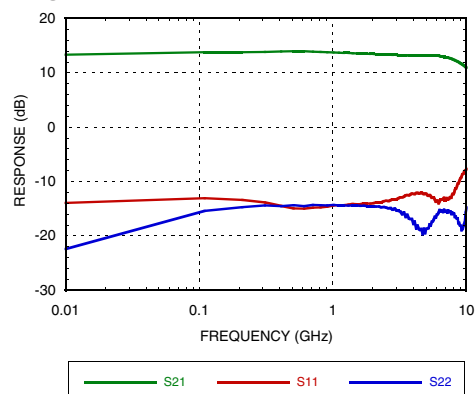
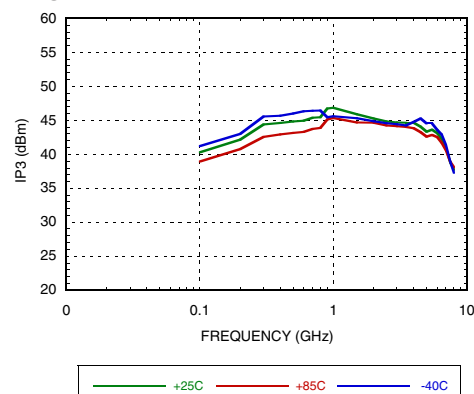
[1] Adjust Vgg1 between -2 to 0V to achieve Idd = 400 mA typical.

[2] Two-Tone Output Power = +10 dBm Each Tone, 1 MHz Spacing.


**GaAs pHEMT MMIC 1 WATT
POWER AMPLIFIER, DC - 6 GHz**
Gain & Return Loss

Gain vs. Temperature

Input Return Loss vs. Temperature

Output Return Loss vs. Temperature

Reverse Isolation vs. Temperature

Noise Figure vs. Temperature




GaAs pHEMT MMIC 1 WATT POWER AMPLIFIER, DC - 6 GHz

P1dB vs. Temperature

Psat vs. Temperature

Output IP3 vs. Temperature

**Gain, Power & Output IP3 vs.
Supply Voltage @ 3 GHz, Fixed Vgg**

**Gain & Return Loss vs. Frequency,
Log Scale**

**Output IP3 vs. Temperature,
Log Scale**




GaAs pHEMT MMIC 1 WATT POWER AMPLIFIER, DC - 6 GHz

Absolute Maximum Ratings

| | |
|--|---------------|
| Drain Bias Voltage (Vdd) | +14 Vdc |
| Gate Bias Voltage (Vgg1) | -3 to 0 Vdc |
| Gate Bias Voltage (Vgg2) | +4 to +7 Vdc |
| RF Input Power (RFIN)(Vdd = +12 Vdc) | +25 dBm |
| Channel Temperature | 175 °C |
| Continuous P _{diss} (T= 85 °C) (derate 95 mW/°C above 85 °C) | 8.6 W |
| Thermal Resistance (channel to ground paddle) | 10.5 °C/W |
| Storage Temperature | -65 to 150 °C |
| Operating Temperature | -40 to 85 °C |
| ESD Sensitivity (HBM) | Class 1B |

Typical Supply Current vs. Vdd

| Vdd (V) | I _{dd} (mA) ^[1] |
|---------|-------------------------------------|
| 11.5 | 400 |
| 12.0 | 400 |
| 12.5 | 400 |

[1] Vgg1 set initially for nominal bias condition of Vdd = +12 V and Vgg2 = +5V to achieve I_{dd} = 400 mA typical. Then adjusting Vdd +/- 0.5 V from 12V to measure I_{dd} variation.



**ELECTROSTATIC SENSITIVE DEVICE
OBSERVE HANDLING PRECAUTIONS**



TOP VIEW

Dimensions: 32, 25, 24, 17, 9, 16, 1, 8, .201, .193, [5.10, 4.90], [5.10, 4.90], .201, .193, .039, .031, [1.00, 0.80], .002, .000, [0.05, 0.00], .003, [0.08], C, -C-

Labels: H637A, XXXX, LOT NUMBER, SEATING PLANE

BOTTOM VIEW

Dimensions: .012, .007, [0.30, 0.18], .140, .135, [3.56, 3.44], .022, .017, [0.56, 0.44], .156, .144, [3.95, 3.65], SQUARE, EXPOSED GROUND PADDLE

Labels: PIN 32, PIN 1

NOTES:

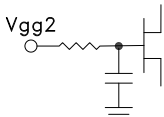
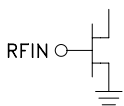
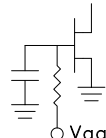
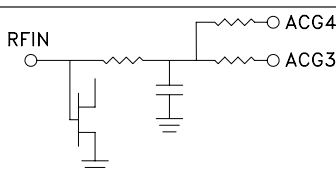
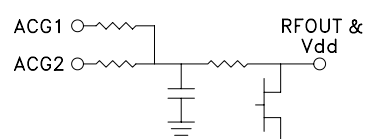

1. LEADFRAME MATERIAL: COPPER ALLOY

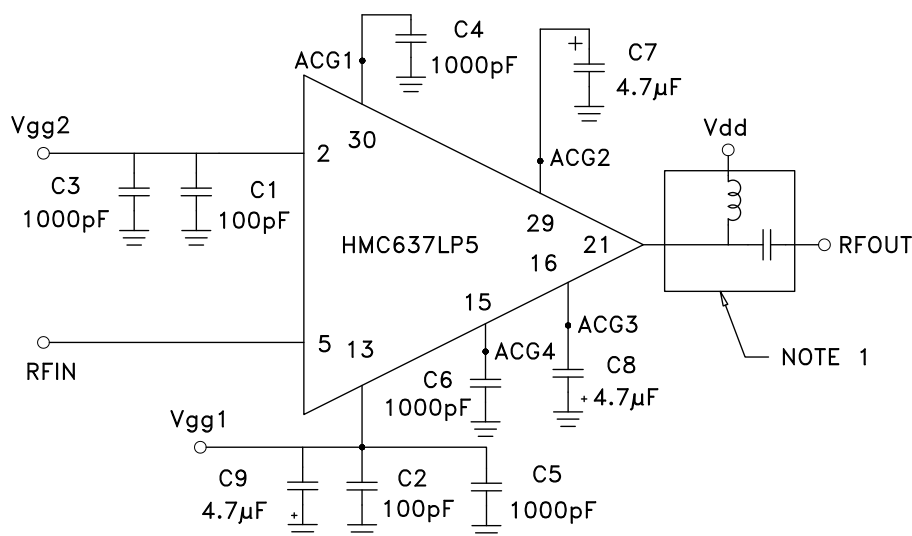
1. LEADFRAME MATERIAL: COPPER ALLOY
2. DIMENSIONS ARE IN INCHES [MILLIMETERS]
3. LEAD SPACING TOLERANCE IS NON-CUMULATIVE
4. PAD BURR LENGTH SHALL BE 0.15mm MAXIMUM.
5. PAD BURR HEIGHT SHALL BE 0.05mm MAXIMUM.
6. PACKAGE WARP SHALL NOT EXCEED 0.05mm.
7. ALL GROUND LEADS AND GROUND PADDLE MUST BE SOLDERED TO PCB RF GROUND.
8. REFER TO HITTITE APPLICATION NOTE FOR SUGGESTED LAND PATTERN

| Part Number | Package Body Material | Lead Finish | MSL Rating | Package Marking ^[2] |
|-------------|--|---------------|---------------------|--------------------------------|
| HMC637ALP5E | RoHS-compliant Low Stress Injection Molded Plastic | 100% matte Sn | MSL3 ^[1] | H637A XXXX |

[2] 4-Digit lot number XXXX


**GaAs pHEMT MMIC 1 WATT
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Pin Descriptions

| Pin Number | Function | Description | Interface Schematic |
|--|-------------|--|---|
| 1, 3, 4, 6 - 12, 14, 17, 18, 19, 20, 22 - 28, 31, 32 | N/C | No connection. These pins may be connected to RF ground. Performance will not be affected. | |
| 2 | Vgg2 | Gate Control 2 for amplifier. +5V should be applied to Vgg2 for nominal operation. Attach bypass capacitor per application circuit herein. |  |
| 5 | RFIN | This pad is DC coupled and matched to 50 Ohms. |  |
| 13 | Vgg1 | Gate Control 1 for amplifier. Attach bypass capacitor per application circuit herein. Please follow "MMIC Amplifier Biasing Procedure" Application Note. |  |
| 15 | ACG4 | Low frequency termination. Attach bypass capacitor per application circuit herein. |  |
| 16 | ACG3 | | |
| 21 | RFOUT & Vdd | RF output for amplifier. Connect the DC bias (Vdd) network to provide drain current (Idd). See application circuit herein. |  |
| 29 | ACG2 | Low frequency termination. Attach bypass capacitor per application circuit herein. | |
| 30 | ACG1 | | |
| Ground Paddle | GND | Ground paddle must be connected to RF/DC ground. |  |


**GaAs pHEMT MMIC 1 WATT
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Application Circuit


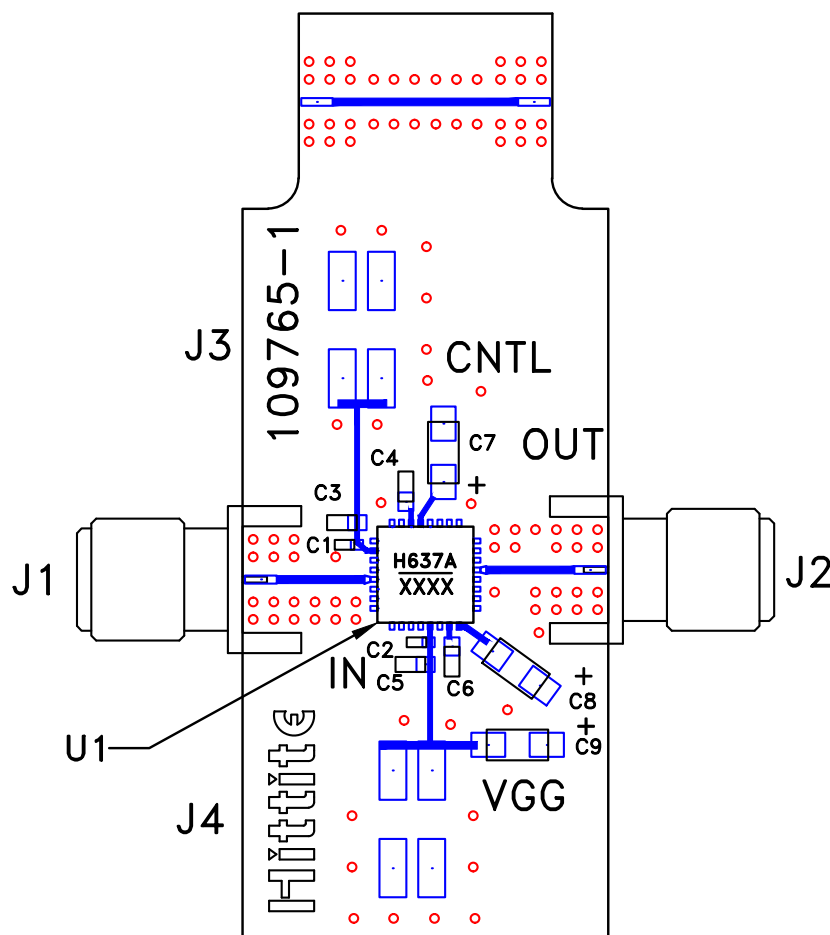
NOTE 1: Drain Bias (Vdd) must be applied through a broadband bias tee or external bias network.

NOTE 2: Power Up Bias Sequence

- A) Set Vgg1 to -2V
- B) Set Vdd to +12V
- C) Set Vgg2 to +5V
- D) Adjust Vgg1 to achieve Idd for 400 mA

Power Down Sequence

- A) Remove Vgg2 Bias
- B) Remove Vdd Bias
- C) Remove Vgg1 Bias


**GaAs pHEMT MMIC 1 WATT
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Evaluation PCB

List of Materials for Evaluation PCB EV1HMC637ALP5 [1]

| Item | Description |
|---------|---------------------------------|
| J1 - J2 | SRI SMA Connector |
| J3 - J4 | 2mm Molex Header |
| C1, C2 | 100 pF Capacitor, 0402 Pkg. |
| C3 - C6 | 1000 pF Capacitor, 0603 Pkg. |
| C7 - C9 | 4.7 μ F Capacitor, Tantalum |
| U1 | HMC637ALP5E |
| PCB [2] | 109765 Evaluation PCB |

[1] Reference this number when ordering complete evaluation PCB

[2] Circuit Board Material: Rogers 4350

The circuit board used in the application should use RF circuit design techniques. Signal lines should have 50 Ohm impedance while the package ground leads and package bottom should be connected directly to the ground plane similar to that shown. A sufficient number of via holes should be used to connect the top and bottom ground planes. The evaluation board should be mounted to an appropriate heat sink. The evaluation circuit board shown is available from Hittite upon request.

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